

AS169-73LF-HX PHEMT GaAs IC SPDT Switch 300 kHz–2.5 GHz

Description

The AS169-73LF-HX is an IC FET SPDT switch housed in a cost-effective SOT-6 plastic package. Featuring low insertion loss, positive voltage operation, and exceptionally low DC power consumption, the AS169-73LF-HX is well-suited for a wide range of telecommunications applications as a general-purpose switch.

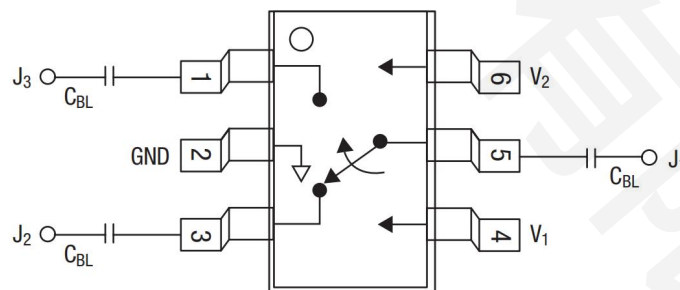
Applications

- ★ General-purpose medium-power switches in telecommunication applications
- ★ T/R switches in 802.11b, g WLAN Bluetooth™ systems

Features

- ★ IP3 52 dBm typical
- ★ P1 dB 30 dBm typical @ 3 V
- ★ Low insertion loss (0.3 dB @ 0.9 GHz)
- ★ Low DC power consumption
- ★ Ultraminiature low-cost SOT-6 plastic package
- ★ Available lead (Pb)-free and RoHS-compliant MSL-1 @ 260 °C per JEDEC J-STD-020

Pin Out



DC blocking capacitors (CBL) must be supplied externally for positive voltage operation. CBL = 100 pF for operation >500 MHz.

Electrical Specifications at 25 °C

$Z_0 = 50 \Omega$, $V_{CTL} = 0/3 V$ unless otherwise noted

Parameter	Frequency	Min	Typ	Max	Unit
Insertion loss ⁽¹⁾	300 kHz–1.0 GHz		0.3	0.4	dB
	300 kHz–2.5 GHz		0.4	0.5	dB
Isolation	300 kHz–1.0 GHz	22	25		dB
	300 kHz–2.5 GHz	21	24		dB
VSWR ⁽²⁾	300 kHz–1.0 GHz		1.15:1	1.25:1	
	300 kHz–2.5 GHz		1.3:1	1.4:1	

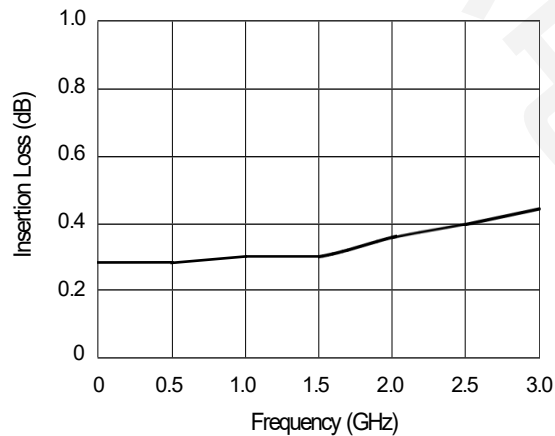
1. Insertion loss changes by 0.003 dB/°C.

2. Insertion loss state.

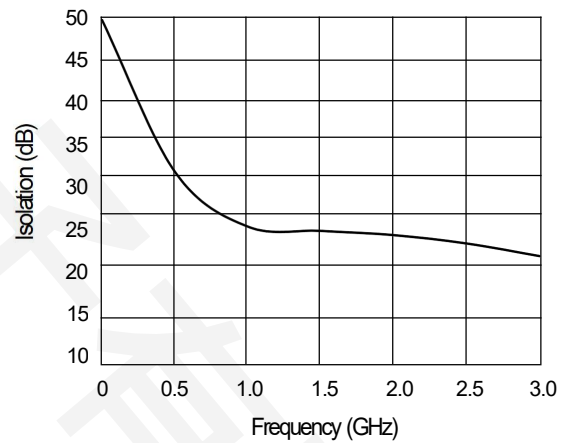
Operating Characteristics at 25 °C (0, 3 V) $Z_0 = 50 \Omega$, $V_{CTL} = 0/3 V$ unless otherwise noted

Parameter	Condition	Frequency	Min	Typ	Max	Unit
Switching characteristics						
Rise, fall time	10/90% or 90/10% RF			25		ns
On, off time	50% CTL to 90/10% RF			35		ns
Video feedthru	$T_{RISE} = 1 \text{ ns}$, BW = 500 MHz			10		mV
Input power for 1 dB compression	$V_{CTL} = 0/3 V$	0.5-2.5 GHz		30		dBm
	$V_{CTL} = 0/5 V$	0.5-2.5 GHz		34		dBm
Intermodulation intercept point (IP3)	Fortwo-tone input power 5 dBm					
	$V_{CTL} = 0/3 V$	0.5-2.5 GHz		43		dBm
	$V_{CTL} = 0/5 V$	0.5-2.5 GHz		50		dBm
Thermal resistance				25		°C/W
ESD rating	Human body model (Class 1A)					
Control voltages	$V_{LOW} = 0 \text{ to } 0.2 V @ 20 \mu A \text{ max.}$ $V_{HIGH} = 3 V @ 100 \mu A \text{ max to } 5 V @ 200 \mu A \text{ max.}$					

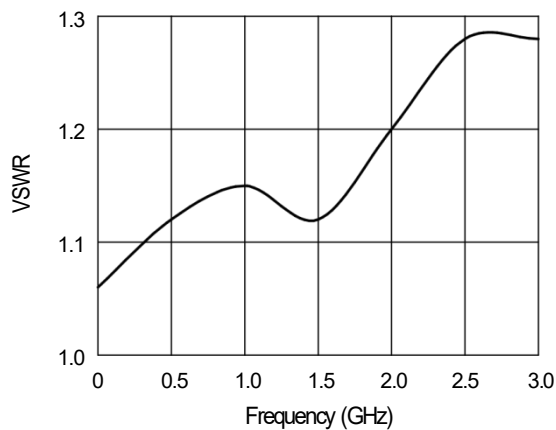
Typical Performance Data (0, 3 V)



Insertion Loss vs. Frequency



Isolation vs. Frequency



VSWR vs. Frequency

Truth Table

V ₁	V ₂	J ₁ -J ₂	J ₁ -J ₃
V _{HIGH}	V _{LOW}	Isolation	Insertion loss
V _{LOW}	V _{HIGH}	Insertion loss	Isolation

All other conditions not recommended.
 $3V \leq V_{HIGH} \leq 5V$, $0V \leq V_{LOW} \leq 0.2V$.

Absolute Maximum Ratings

Characteristic	Value
RF input power	6W > 500 MHz 0/7 V control
Control voltage	-0.2 V, +8 V
Operating temperature	-40 °C to +85 °C
Storage temperature	-65 °C to +150 °C

Performance is guaranteed only under the conditions listed in the specifications table and is not guaranteed under the full range(s) described by the Absolute Maximum specifications. Exceeding any of the absolute maximum/minimum specifications may result in permanent damage to the device and will void the warranty.

CAUTION: Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions must be employed at all times.

AS169-73LF-HX SOT-6

